ERRATA

Erratum: Fowler-Nordheim electron tunneling in thin Si-SiO₂-Al structures
[J. Appl. Phys. 52, 5710 (1981)]

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PACS numbers: 73.40.Gk, 99.10. + g

On Fig. 6, page 5716 the value of \( m_\text{ox} = 1.03 \) \( m_e \) is incorrect, resulting from a calculation error. The correct value should be of the order of 0.5 \( m_e \). We would like to thank Dr. Z. Weinberg from IBM for observing this error, and notifying us.

Erratum: A kinetic study of the plasma-etching process. I. A model for the etching of Si and SiO₂ in CₜFₘ/H₂ and CₜFₘ/O₂ plasmas
[J. Appl. Phys. 53, 2923 (1982)]

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The label for the horizontal axis of Fig. 11 is in error. The species symbols for CF₄ and H₂ should be exchanged so that the fraction of CF₄ decreases from left to right and the fraction of H₂ increases from left to right.

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